

Revision 1.06

SINGLE FREQUENCY LASER DIODES Distributed Feedback Laser



General Product Information

Spectroscopy
Metrology
THz Generation



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	T _S	°C	-40		85
Operational Temperature at Case	T_{C}	°C	-20		75
Operational Temperature at Laser Chip	T_{LD}	°C	5		50
Forward Current	I _F	mA			270
Reverse Voltage	V_R	V			2
Output Power	P_{opt}	mW			160
TEC Current	I _{TEC}	Α			1.8
TEC Voltage	V_{TEC}	V			3.2

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T_{case}	°C	-20		65
Operational Temperature at Laser Chip	T_{LD}	°C	5		45
Forward Current	I _F	mA			250
Output Power	P _{opt}	mW	30		150

Measurement Conditions / Comments
measured by integrated Thermistor

Characteristics at T_{LD} = 25° at BOL

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm	851	852	853
Linewidth (FWHM)	Δλ	MHz		2	
Mode-hop free Tuning Range	$\Delta \lambda_{\text{tune}}$	pm		1500	
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.06	
Current Coefficient of Wavelength	dλ / dl	nm / mA		0.003	
Sidemode Supression Ratio	SMSR	dB	30	45	

Measurement Conditions / Comments
see images on page 4
reached by temperature modulation
$P_{opt} = 150 \text{ mW}$





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Characteristics at T _{LD} = 25° a	at BOL				cont'd
Parameter	Symbol	Unit	min	typ	max
Mode-hop free Temperature Range	T_{LD}	° C	15		40
Mode-hop free Power Range	P _{opt}	mW	30		150
Laser Current @ P _{opt} = 150 mW	I_{LD}	mA			250
Slope Efficiency	η	W/A	0.6	0.8	1.0
Threshold Current	I _{th}	mA			70
Divergence parallel (FWHM)	$\Theta_{ }$	0		8	
Divergence perpendicular (FWHM)	Θ_{\perp}	0		21	
Degree of Polarization	DOP	%		90	

Measurement Conditions / Comments
Temperature at Laser Chip
parallel to short axis of the housing (see p. 3)
parallel to long axis of the housing (see p. 3)
150 mW; E field perpendicular to long axis of housing

Symbol	Unit	min	typ	max
I _{mon} / P _{opt}	μΑ/mW	1		20
				, , , , , , , , , , , , , , , , , , ,

1eas	urement Conditions / Comments
$_{R} =$	5 V

Thermoelectric Cooler					
Parameter	Symbol	Unit	min	typ	max
Current	I _{TEC}	А		0.4	
Voltage	U_TEC	V		0.8	
Power Dissipation (total loss at case)	P _{loss}	W		0.5	
Temperature Difference	ΔΤ	K			50

Measurement Conditions / Comments
$P_{opt} = 150 \text{ mW}, \Delta T = 20 \text{ K}$
$P_{opt} = 150 \text{ mW}, \Delta T = 20 \text{ K}$
$P_{opt} = 150 \text{ mW}, \Delta T = 20 \text{ K}$
$P_{opt} = 150 \text{ mW}, \Delta T = T case - TLD $

Parameter	Symbol	Unit	min	typ	max
Resistance	R	kΩ		10	
Beta Coefficient	β			3892	
Steinhart & Hart Coefficient A	А		1.1293 x 10 ⁻³		
Steinhart & Hart Coefficient B	В		2.3410 x 10 ⁻⁴		
Steinhart & Hart Coefficient C	C		;	3.7755 x 10	-8

Measurement Conditions / Comments					
$T_{LD} = 25^{\circ} C$					
$R_1 / R_2 = e^{ \beta (1/T_1 - 1/T_2)} $ at $T_{LD} =$	0° 50° C				
$1/T = A + B(\ln R) + C(\ln R)^3$					
T: temperature in Kelvin					
R: resistance at T in Ohm					

Thermistor (Standard NTC Type)

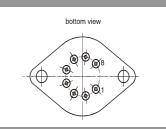


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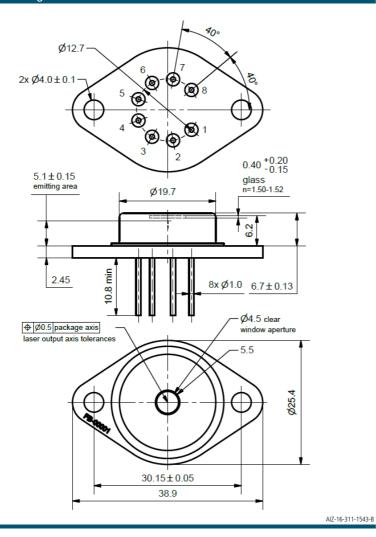
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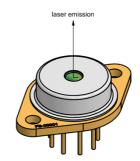


Pin Assignment							
1	Thermoelectric Cooler (+)	5	Laser Diode Anode				
2	Thermistor	6	Monitor Diode Anode				
3	Thermistor	7	Photo Diode Cathode				
4	Laser Diode Cathode	8	Thermoelectric Cooler (-)				
ΔII	8 pins are isolated from case						



Package Drawings





DNV-GL

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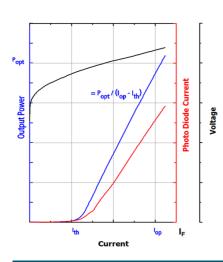
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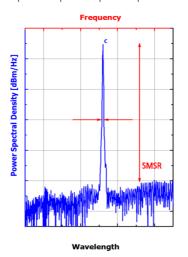


Typical Measurement Results

Output Power vs. Current



Spectra at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Ordering Information:



800 Village Walk #316 Guilford, CT 06437 Ph: 203-401-8093

Email orders to: sales@xsoptix.com
Fax orders to: 800-878-7282

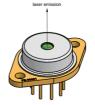
Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The DFB laser is sensitive against optical feedback, so an optical isolator may be required in order to avoid any disturbance of the emission spectrum. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.







INVISIBLE LASER RADIATION AVOID EYE OR SKIN EXPOSURE TO DIRECT OR SCATTERED RADIATION CLASS 4 LASER PRODUCT WAVELENGTH 852 nm MAX. OUTPUT POWER 160 mW





